TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7SLU04F, TC7SLU04FU

INVERTER

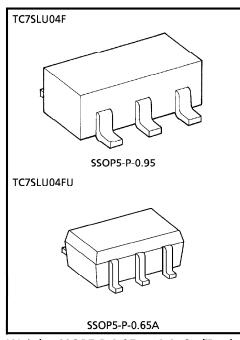
The TC7SLU04 is a low voltage operative C^2MOS INVERTER fabricated with silicon gate C^2MOS technology. Operating voltage (V_{CC} (opr)) is $1\sim 3V$ equivalent to 1pc or 2pcs of dry cell battery and it achives low power dissipation.

The internal circuit is composed of single stage inverter, it can be applied for C, R oscillator circuits, crystal oscillator circuits, and linear amplifiers.

The input is equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

- High Speed ······ t_{pd} = 10ns (Typ.)
 at V_{CC} = 3V
- Low Power Dissipation $\cdots I_{CC} = 1\mu A$ (Max.) at Ta = 25°C
- High Noise Immunity ············ V_{NIH} = V_{NIL}
 = 10% V_{CC} (Min.)
- Symmetrical Output Impedance ······ |IOH| = IOL = 1mA
- \bullet Balanced Propagation Delay Time $\cdots t_{pLH} \dot = t_{pHL}$
- Low Voltage Operating············V_{CC (opr)} = 1~3.6V

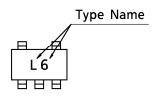


Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A : 0.006g (Typ.)

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	Vcc	-0.5~5	V
DC Input Voltage	v_{IN}	-0.5~V _{CC} +0.5	V
DC Output Voltage	Vout	-0.5~V _{CC} +0.5	V
Input Diode Current	ΙΚ	± 20	mA
Output Diode Current	lok	± 20	mA
DC Output Current	IOUT	± 12.5	mA
DC V _{CC} /Ground Current	lcc	± 25	mA
Power Dissipation	PD	200	mW
Storage Temperature	T _{stg}	-65∼150	°C
Lead Temperature (10s)	TL	260	°C

MARKING

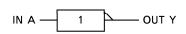


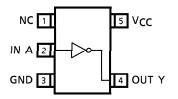
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LOGIC DIAGRAM

PIN CONNECTION (TOP VIEW)





RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	Vcc	1~3.6	V
Input Voltage	V _{IN}	0~V _{CC}	V
Output Voltage	VOUT	0~V _{CC}	V
Operating Temperature	T _{opr}	- 40~85	°C

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	TEST	TEST CONDITION V _{CC}		Т	a = 25°	С	Ta = -4	LINUT			
CHARACTERISTIC SYMBOL				CIR- CUIT	Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High-Level Input					1.0	0.85	_	_	0.85	_	
Voltage VIH	VIH	_	_		1.5 3.0	1.20	_	 	1.20	_	V
						2.40	_		2.40	_	
Low-Level Input			_		1.0	—	_	0.15	—	0.15	
Voltage	V _{IL}	_			1.5	—	—	0.30	—	0.30	V
Voltage					3.0	_	_	0.60		0.60	
				I _{OH} = -20μA	1.0	0.8	1.0	—	0.8	l —	V
High-Level	V _{OH}		V _{IN} = V _{IL}		1.5	1.3	1.5	—	1.3	_	
1		_			3.0	2.7	2.9	_	2.7	_	
Output Voltage				$I_{OH} = -1mA$	1.5	1.07	1.23	_	0.99	_	
				$I_{OH} = -2.6mA$	3.0	2.61	2.68	—	2.55	_	
			V _{IN} = V _{IH}		1.0	-	0.0	0.2	<u> </u>	0.2	
l avv l aval				$I_{OL} = 20 \mu A$	1.5	l —	0.0	0.2	l —	0.2	
Output Voltage	VOL	_			3.0	l —	0.1	0.3	—	0.3	V
				I _{OL} = 1mA	1.5	_	0.23	0.31	<u> </u>	0.37	
				$I_{OL} = 2.6 mA$	3.0	l —	0.23	0.31	l —	0.33	
Input Leakage Current	I _{IN}	_	V _{IN} = V _{CC}	or GND	3.6	_	_	± 0.1	_	± 1.0	
Quiescent Supply Current	lcc		V _{IN} = V _{CC}	or GND	3.6		_	1.0	_	10.0	μ A

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 The information contained herein is subject to change without notice.

AC ELECTRICAL CHARACTERISTICS ($C_L = 15pF$, Input $t_r = t_f = 6ns$, $V_{CC} = 3.3 \pm 0.3 V$)

CHARACTERISTIC SYMBOL	CVMDOL	TEST	TEST CONDITION		UNIT		
	CUIT	1231 CONDITION	MIN.	TYP.	MAX.	UNIT	
Output Transition	tTLH				6.0	9.0	ns
Time	tTHL	_	_		0.0	9.0	113
Propagation	^t PLH				4.0	13.0	nc
Delay Time	t _{PHL}		1		4.0	13.0	ns

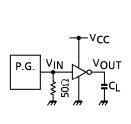
AC ELECTRICAL CHARACTERISTICS ($C_L = 25pF$, Input $t_r = t_f = 6ns$)

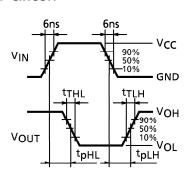
CHARACTERISTIC SYMBOL	SVMBOL	TEST	TEST CONDITION		Ta = 25°C		C	Ta = -4		
	CIR- CUIT	1231 CONDITION	V_{CC}	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT	
Output Transition	4			1.0	_	50	150	_	240	
Output Transition Time	t _{TLH}	_	_	1.5		23	45	<u> </u>	55	ns
Time	tTHL			3.0		10	15		20	
Proposition	4			1.0	_	50	100	_	150	
Propagation Delay Time	t _{PLH}	_	_	1.5	_	20	40	l —	50	ns
Delay Time	t _{PHL}			3.0	_	8	15	_	20	
Input Capacitance	CIN	_	_		_	5	10		10	
Power Dissipation	Coo		Note (1)			10				pF
Capacitance	C _{PD}					10				

Note (1): CpD defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

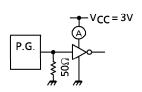
Average operating current can be obtained by the equation as follows. $I_{CC}(opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

SWITCHING CHARACTERISTICS TEST CIRCUIT





ICC (opr) TEST CIRCUIT

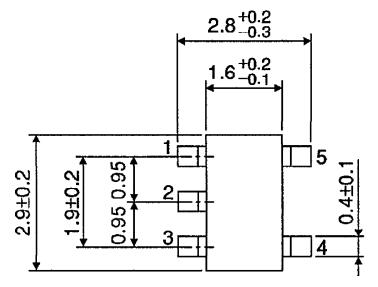


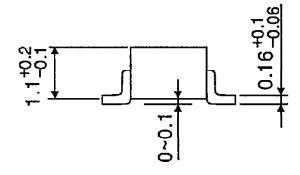
Input waveform is the same as that in case of switching characteristics test.

OUTLINE DRAWING

SSOP5-P-0.95

Unit: mm

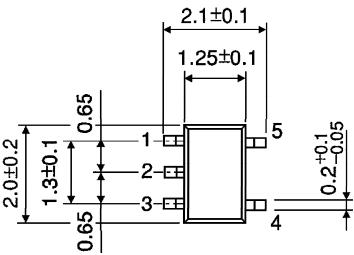




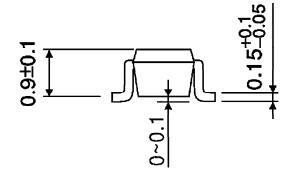
Weight: 0.016g (Typ.)

OUTLINE DRAWING

SSOP5-P-0.65A



Unit: mm



Weight: 0.006g (Typ.)